Rev.D Nov.-2015

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SOT-89 NPN Silicon NPN transistor in a SOT-89 Plastic Package.

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, 2SB1132

Low saturation voltage, complements the 2SB1132.

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Medium power amplifier applications.

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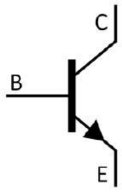

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PIN1 Base PIN 2 Collector PIN 3 Emitter

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h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82 180	120 270	180 390
Marking	HDAP⁑	HDAQ⁑	HDAR⁑

[illegible]

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	32	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current-Continuous	I_C	1.0	A
Collector Base-Continuous(Pulse)	I_{CP}	2.0	A
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation	P_C(Tc=25)	2.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

[illegible]

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=50 A I_E=0	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	32			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=50 A I_C=0	5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=20V I_E=0			0.5	A
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=4.0V I_C=0			0.5	A
DC Current Gain	h_{FE}	V_{CE}=3.0V I_C=100mA	82		390	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA I_B=50mA		0.15	0.4	V
Transition Frequency	f_T	V_{CE}=5.0V I_C=50mA f=100MHz		150		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V I_E=0 f=1.0MHz		15		pF

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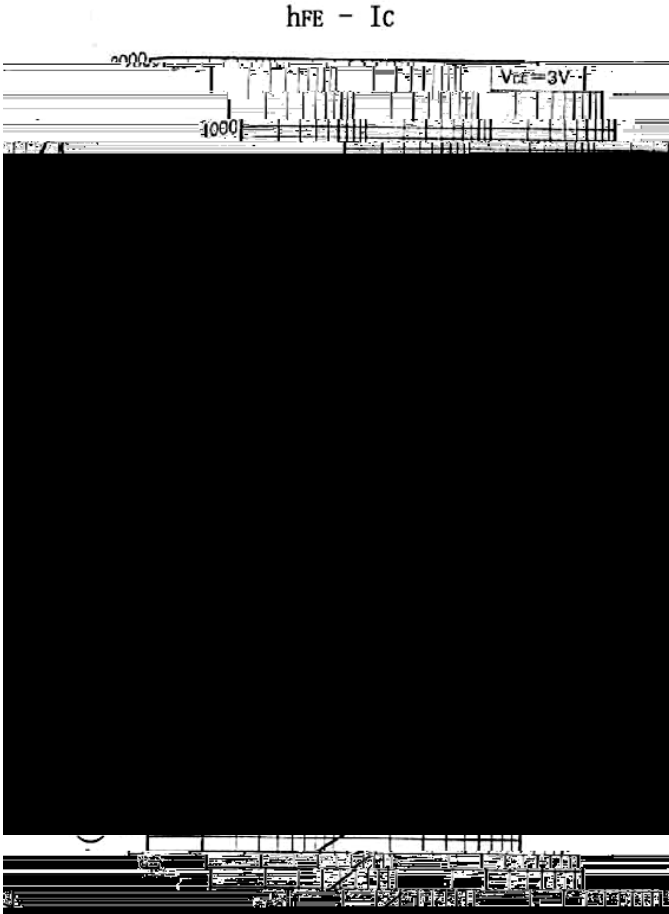

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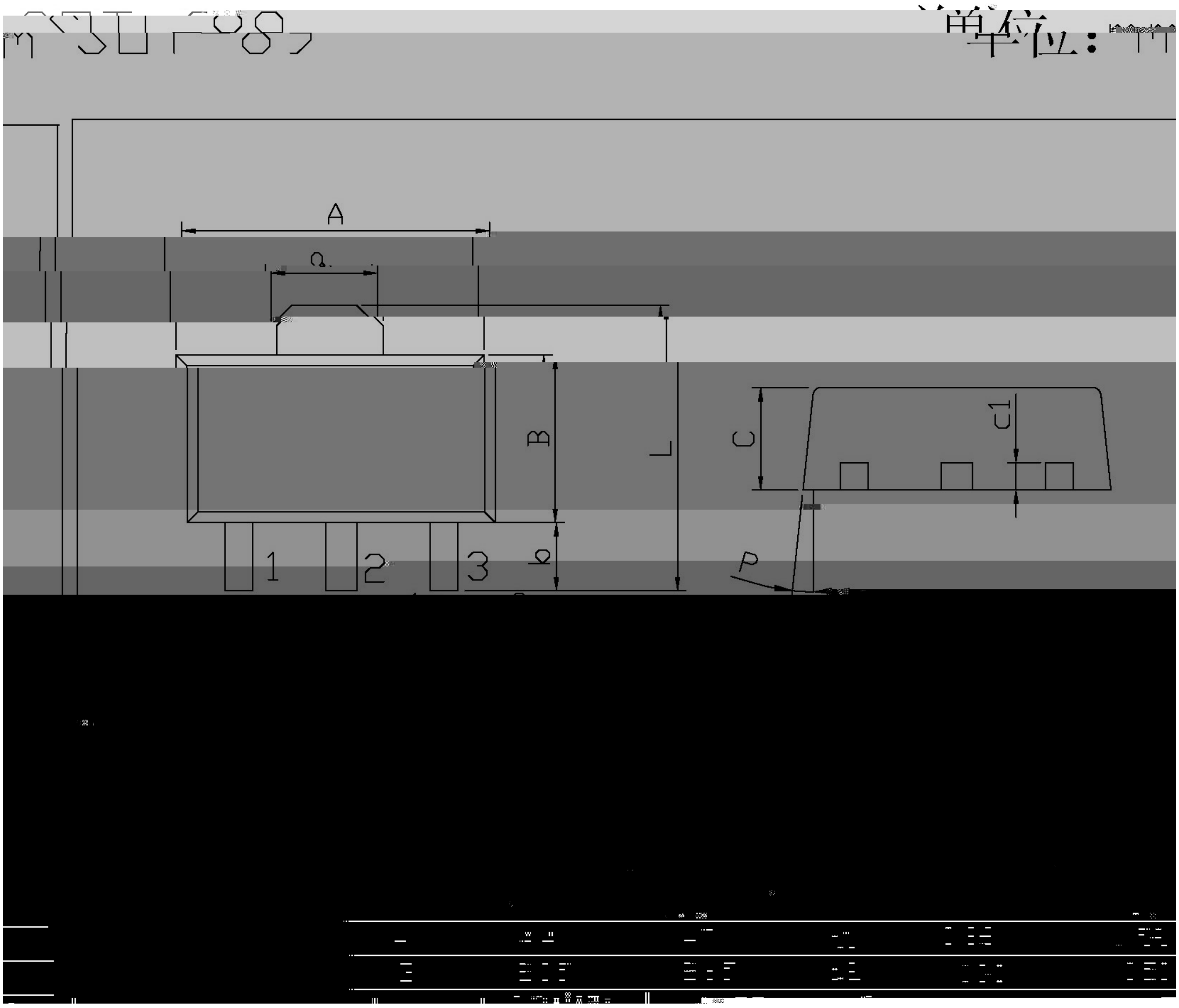

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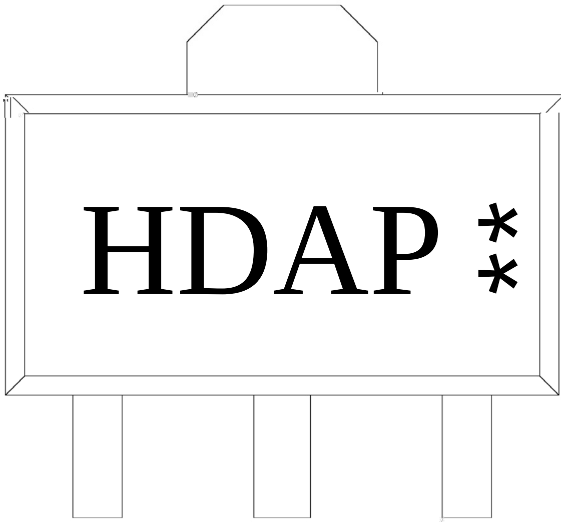

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DA

P h_{FE}

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Note:

H:	Company Code.
DA:	Product Type.
P	h_{FE} Classifications Symbol
**:	Lot No. Code, code change with Lot No.

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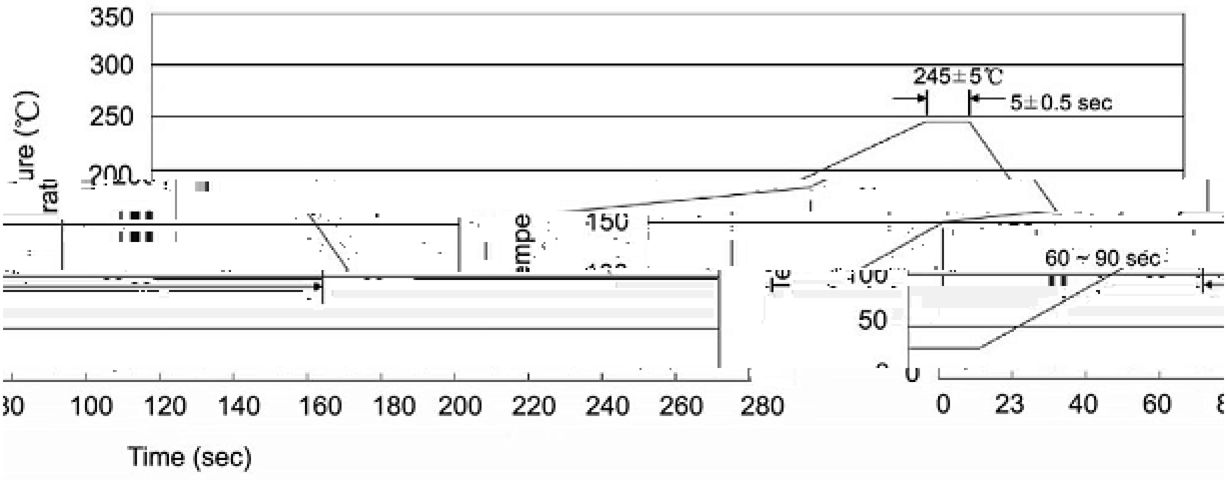

	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

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